

Bi-directional ESD Protection Diode

DESCRIPTIONS

The TESDL3V3B23P1Q0 is Bidirectional ESD rated clamping cell to protect power interfaces, or one control line, or one low speed data line in an electronic system. It has been specifically designed to protect sensitive electronic components which are connected to power and control lines from over-voltage damage by Electrostatic Discharging (ESD), and Lightning.

TESDL3V3B23P1Q0 is a unique design which includes proprietary clamping cells in a small package. During transient conditions, the proprietary clamping cells prevent over-voltage on the control/data/power lines, protecting any downstream components.

The TESDL3V3B23P1Q0 may be used to provide ESD protection up to \pm 30kV (contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 8.2A (8/20µs) according to IEC61000-4-5.

FEATURES

- ESD protect for 1 line with bidirectional.
- Provide ESD protection for each channel to IEC61000-4-2 (ESD) ±30kV (air), ±30kV (contact) IEC61000-4-5 (Lightning) 8.2A (8/20µs)
- Suitable for 3.3V and below, operating voltage applications
- Ultra small package saves board space.
- Protect one I/O line or one power line.
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-Free

APPLICATION

- Computers and peripherals
- Control Signal Lines Protection
- Power lines on PCB Protection
- Serial and Parallel Ports Protection



PACKAGE: DFN0603-2L	PIN CONFIGURATION	CIRCUIT DIAGRAM
63	PIN 1 PIN 2	PIN 1 • PIN 2



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ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	VALUE	UNIT			
Peak pulse power (tp = 8/20us)	Ррк	70	W			
Peak pulse current (tp = 8/20us)	IPP	8.2	А			
ESD according to IEC61000-4-2 air discharge	Vesd	±30	kV			
ESD according to IEC61000-4-2 contact discharge	VESD	±30	kV			
Junction temperature range	TJ	-55 to +150	°C			
Storage temperature range	T _{STG}	-55 to +150	°C			

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Reverse working voltage		Vrwm	-	-	3.3	V
Reverse breakdown voltage	$I_R = 1mA$, $T_J = 25^{\circ}C$	VBR	4	-	-	V
Reverse leakage current	V _{RWM} = 3.3V	I _R	-	-	100	nA
Clamping voltage ⁽¹⁾	I _{PP} = 4.0A, tp = 8/20us	Vc	-	-	7.3	V
	I _{PP} = 8.2A, tp = 8/20us		-	-	8.5	V
Clamping voltage ⁽²⁾	I _{TLP} = 4A, tp = 100ns	VcL	-	5.72	-	V
	$I_{TLP} = 16A$, tp = 100ns		-	9.51	-	V
Junction capacitance	$1MHz, V_R = 0V$	CJ	-	17	23	pF
Dynamic resistance ⁽²⁾		Rdyn	-	0.32	-	Ω

Notes:

1. Non-repetitive current pulse, according to IEC61000-4-5.

2. TLP parameter: $Z_0 = 50 \Omega$, tp = 100ns, tr = 2ns, averaging window from 60ns to 80ns. RDYN is calculated from 4A to 16A.

ORDERING INFORMATION				
ORDERING CODE	PACKAGE	PACKING		
TESDL3V3B23P1Q0 M3G	DFN0603-2L	10,000 / 7" Reel		



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

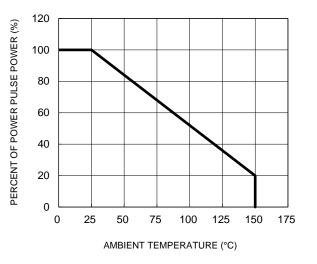


Fig.3 Clamping Voltage vs. Peak Pulse Current

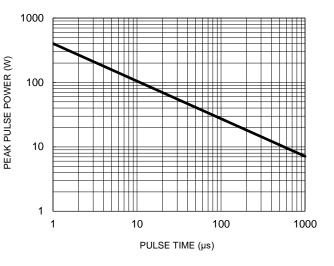


Fig.4 Capacitance vs. Reverse Voltage

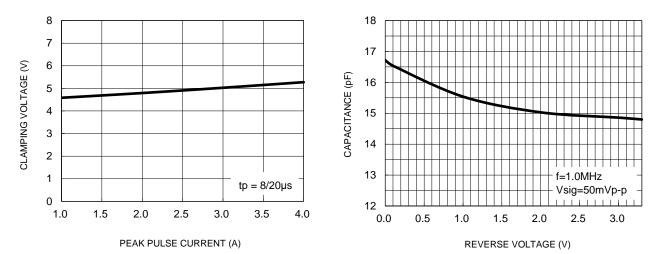


Fig.5 TLP Curve

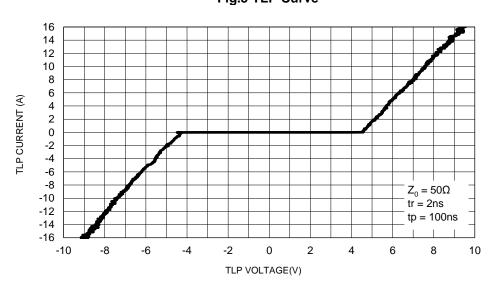


Fig.1 Peak Pulse Power vs. Junction Temperature Fig.2 Non-Repetitive Peak Pulse Power vs. Pulse Time



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.6 8/20µs pulse waveform per IEC61000-4-5

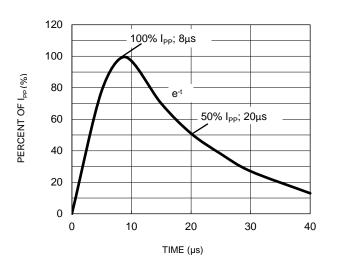
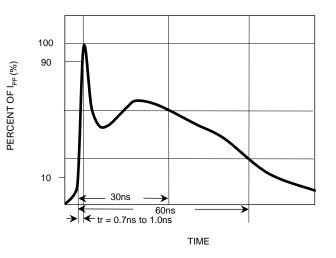


Fig.7 ESD pulse waveform per IEC61000-4-2





APPLICATION INFORMATION

Device Connection

The TESDL3V3B23P1Q0 is designed to protect one line against system ESD Lightning pulses by clamping it to an acceptable reference. It provides bidirectional protection.

The usage of the TESDL3V3B23P1Q0 is shown in Fig1.Protected line, such as data line, control line, or power line. In order to minimize parasitic inductance in the board traces, all path lengths connected to the pins of TESDL3V3B23P1Q0 should be kept as short as possible.

In order to obtain enough suppression of ESD induced transient, good circuit board is critical. Thus, the following guidelines are recommended:

- Let the path length between the protected lines and the TESDL3V3B23P1Q0 minimize.
- Place the TESDL3V3B23P1Q0 near the input terminals or connectors to restrict transient coupling.
- The ESD current return path to ground should be kept as short as possible.
- Use ground planes whenever possible.

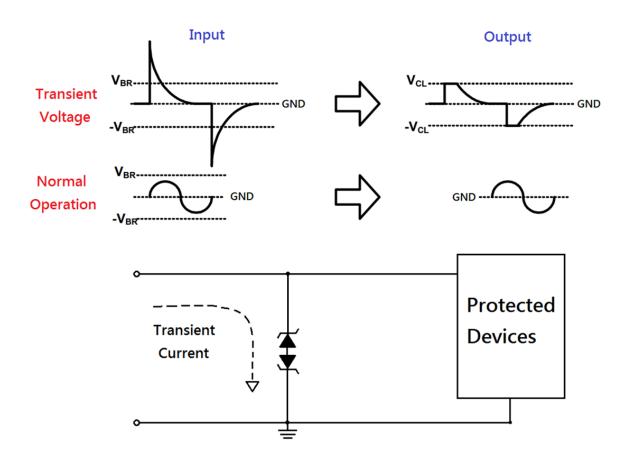
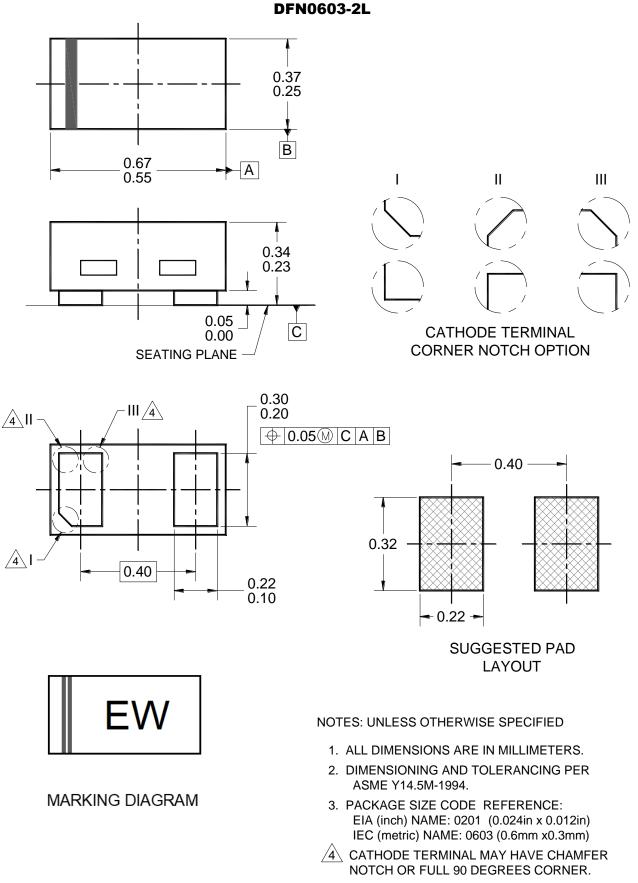


Fig.1 ESD protection by TESDL3V3B23P1Q0

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PACKAGE OUTLINE DIMENSIONS



5. DWG NO. REF: HQ2SD07-DFN0603-067 REV B.



TESDL3V3B23P1Q0

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